

**7-20GHz Medium Power Amplifier
GaAs Monolithic Microwave IC**

preliminary

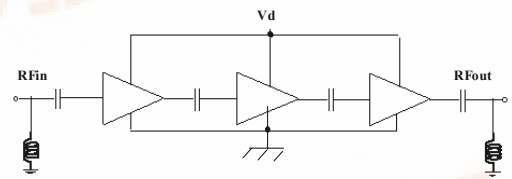
Description

The CHA3667a is a wide band monolithic medium power amplifier.

It is designed for a wide range of applications, from military to commercial communication systems. The circuit is manufactured with a Power-HEMT process, 0.15µm gate length, via hole through the substrate.

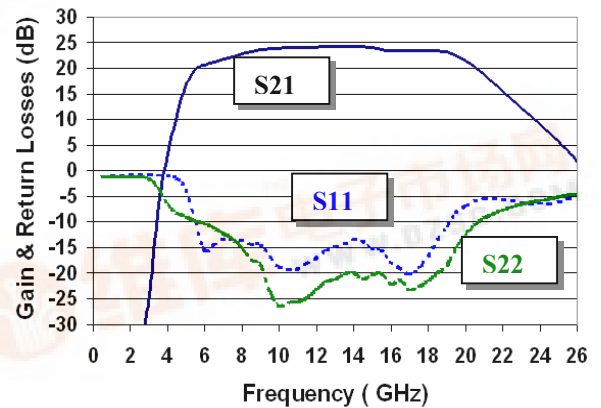
It is ESD protected on RF ports thanks to DC specific filter circuits .

It is supplied in chip form.



Main Features.

- Broadband performance 7-20GHz
- Self biased
- 23dB gain @2.7dB noise figure
- 20 dBm Output power at 1dB compression
- DC power consumption, 175 mA @4.2V
- Chip size:2,45 x1,21x0,1 mm



Main Characteristics

Tamb. = 25°C, Vd = 4.2V

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Input frequency range	7		20	GHz
G	Small signal gain		23		dB
NF	Noise Figure		2.7		dB
P-1dB	Output power at 1dB gain compression		20		dBm
Id	Bias current		175		mA

ESD Protections : Electrostatic discharge sensitive device observe handling precautions !

Electrical Characteristics on wafer



CHA3667a

7-20GHz Amplifier

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Tamb. = 25°C, Vd = 4.2V

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	7		20	GHz
G	Gain				dB
	(7-8 GHz)		21		
	(8-20 GHz)		23		
NF	Noise figure (7-18 GHz)		2.5		dB
	Noise figure (19-20 GHz)		3		dB
RLin	Input Return Loss		-10 (1)		dB
RLout	Output Return Loss		-10		dB
IP3	Output IP3		28		dBm
P1dB	Pout at 1dB gain compression:				
	(7-13 GHz)		20		dBm
	(14-20 GHz)		21		dBm
Isol	Reverse isolation		45		dB
Vd	Drain bias voltage		4.2		V
Id	Drain bias current		175		mA

These values are representative for on wafer measurements that are made without bonding wires at the RF ports.

(1) Typical Rlin at 20GHz is -8dB

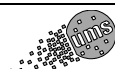
*preliminary***Absolute Maximum Ratings (1)**

Tamb. = +25°C

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	4.5	V
Id	Drain bias current	240	mA
Pin	RF input power (2)	3	dBm
Tch	Maximum channel temperature	+175	°C
Ta	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +125	°C

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Duration < 1s

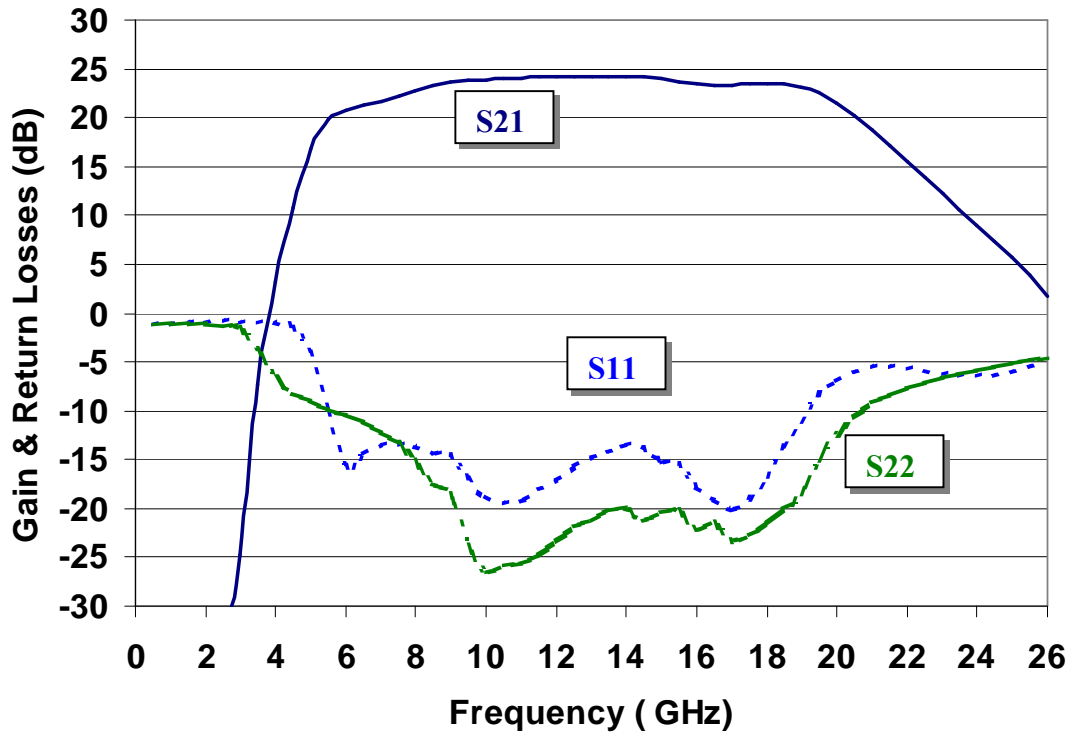


Typical Measured Performance

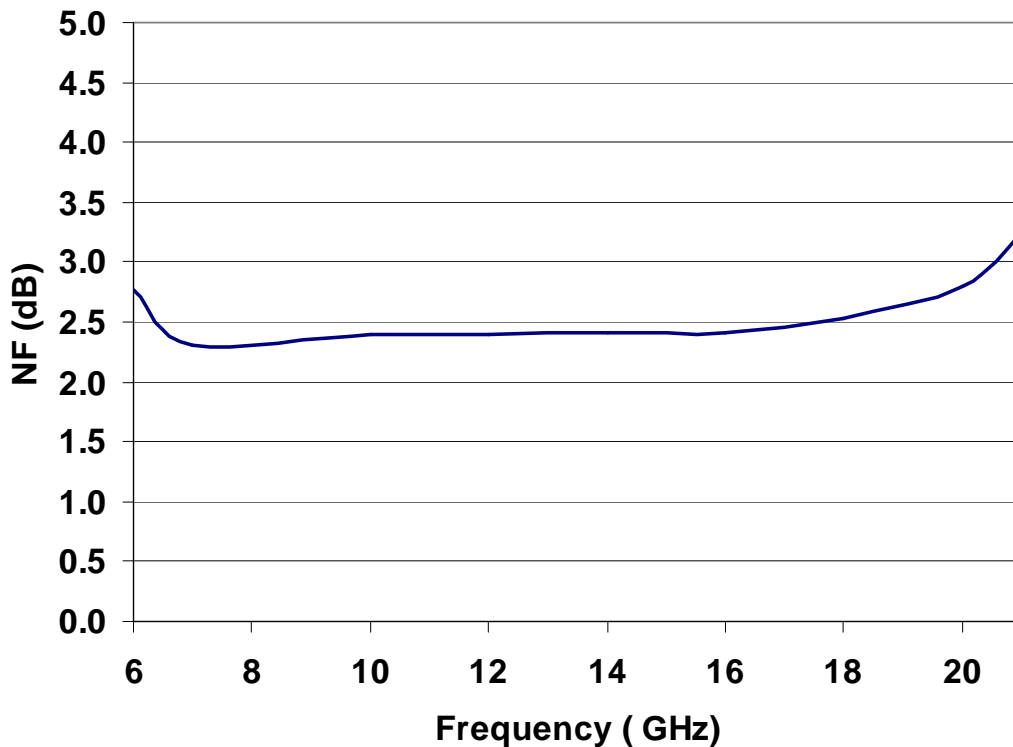
On wafer measurement (without bonding wires at the RF ports)
 Tamb.=+25°C, Vd=+4.2V Id=175mA

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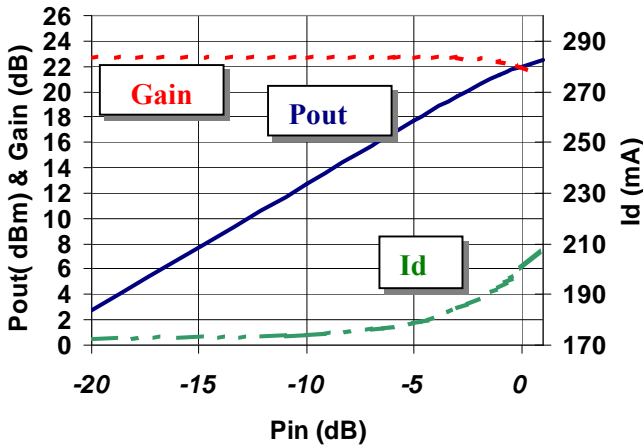
Gain & Return Losses versus frequency



Noise Figure versus Frequency

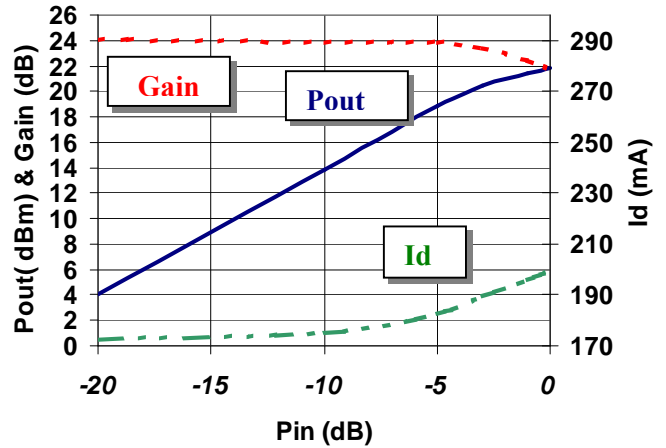


Pout, Gain & Id versus Pin @ 7GHz

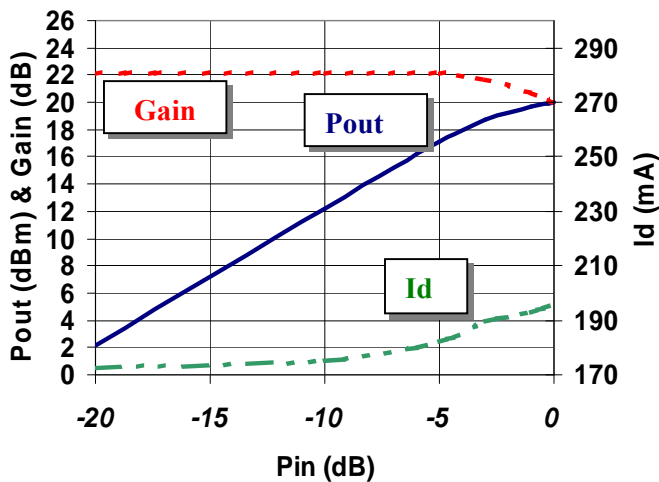


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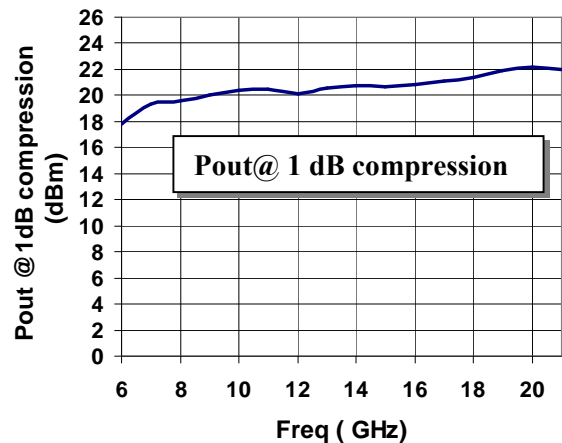
Pout, Gain & Id versus Pin @ 16GHz



Pout, Gain & Id versus Pin @ 20GHz



Output Power @ 1dB compression versus Frequency



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Typical Chip on wafer Sij parameters

Tamb.=+25°C, Vd1=+4.2V, Id=175mA

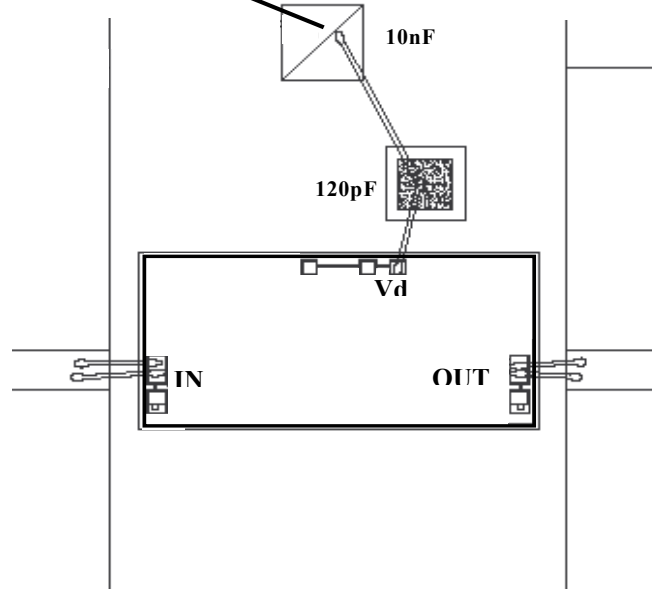
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Freq (GHz)	dBS11 (dB)	PhS11 (°)	dBS21 (dB)	PhS21 (°)	dBS12 (dB)	PhS12 (°)	dBS22 (dB)	PhS22 (°)
1	-1.2	137.6	-60.8	116.0	-61.8	119.4	-1.3	139.8
2	-1.0	64.1	-59.4	-145.5	-65.2	125.0	-1.2	67.6
3	-0.9	5.0	-34.5	-82.6	-79.0	6.5	-1.3	7.0
4	-0.9	-48.9	-7.3	-103.5	-57.8	137.2	-3.5	-55.9
5	-1.5	-115.5	10.8	130.8	-58.0	134.0	-8.2	-80.3
6	-10.0	127.5	19.8	-1.5	-66.7	127.6	-9.9	-98.5
7	-14.5	-26.5	21.2	-97.9	-63.3	58.3	-11.2	-121.3
8	-13.6	-74.8	22.2	-169.1	-51.0	-57.2	-13.3	-143.3
9	-14.5	-98.8	23.3	128.6	-60.3	-47.0	-17.5	-160.1
10	-17.0	-116.1	23.8	70.9	-54.8	153.4	-23.7	-173.6
11	-19.4	-108.1	24.0	18.2	-49.7	170.8	-25.8	-147.8
12	-18.1	-93.3	24.1	-30.6	-61.4	40.1	-24.8	-124.2
13	-15.6	-91.5	24.2	-77.3	-71.6	-148.0	-21.8	-129.3
14	-14.2	-105.9	24.2	-123.1	-57.8	78.5	-20.2	-153.6
15	-13.8	-128.5	24.2	-169.3	-51.3	172.9	-21.3	169.4
16	-15.6	-159.4	23.6	145.7	-46.4	126.1	-20.2	116.4
17	-19.1	164.0	23.4	103.3	-44.0	63.4	-21.5	56.6
18	-19.0	113.6	23.5	59.3	-50.5	-40.7	-22.7	42.6
19	-13.6	47.5	23.4	10.5	-55.8	-78.9	-20.0	43.3
20	-8.2	1.6	22.5	-43.8	-45.0	-133.1	-15.0	27.7
21	-6.0	-38.0	20.3	-97.5	-47.5	-157.9	-10.6	6.1
22	-5.5	-66.9	17.2	-145.8	-51.0	127.1	-8.4	-16.1
23	-5.9	-85.7	13.8	170.9	-48.5	119.3	-7.1	-36.5
24	-6.5	-97.8	10.6	130.5	-51.4	70.7	-6.2	-51.7
25	-6.5	-104.0	7.4	90.0	-55.3	88.6	-5.5	-66.0
26	-5.5	-113.5	3.9	48.3	-49.9	32.8	-4.8	-79.5

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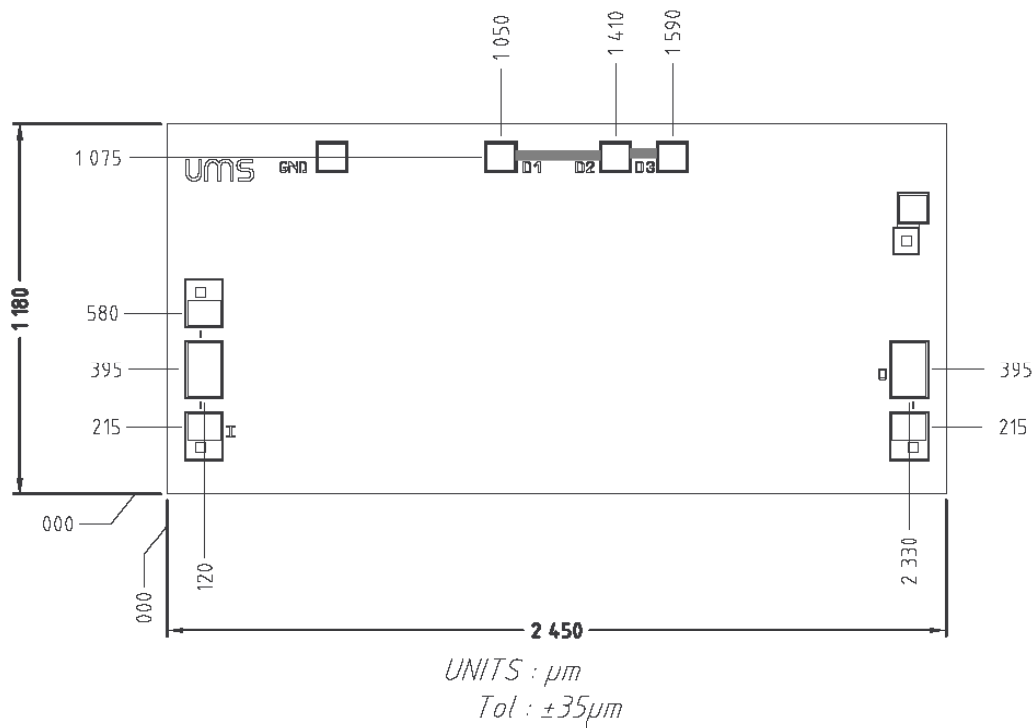
Chip Assembly and Mechanical Data

DC drain supply feed



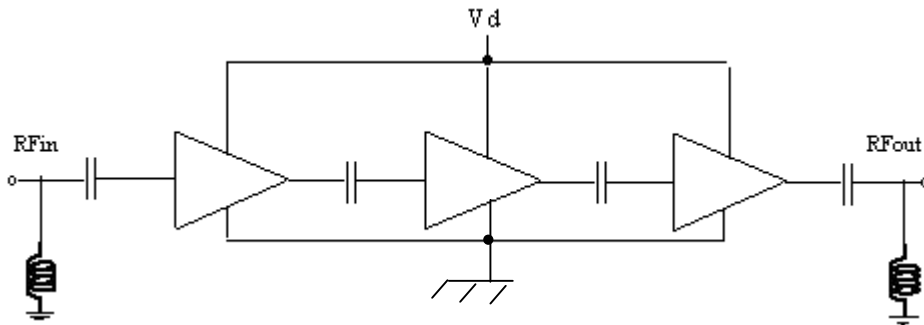
- Note : 25µm diameter gold wire is to be preferred.
- DC Pad size : 86/83µm .
- RF Pad size: 105/171µm
- RF wire bondings should be as short as possible, lower than 0.35mm.
- Chip thickness: 100µm ±.10µm

Bonding pad position



*preliminary***Notes**

-Due to ESD protection circuits on RF input and output, an external capacitance might be requested to isolate the product from external voltage that could be present on the RF accesses.



-Due to BCB coating on the chip, qualification domain implies the chip must be glued.

Ordering Information

Chip form: CHA3667a98F/00

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